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April 1st, 2010
Renesas Electronics Corporation

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M16C/62

Programming the M16C/62 Flash in CPU Rewrite Mode

1.0 Abstract

The following article describes CPU Rewrite Mode on the M16C/62 (M30624FG), which allows erasing and programming the on-chip flash memory under control of a user's program. It is assumed that the microcontroller is operating in "single chip" mode. A short program, targeted for the MSV1632 Starter Kit, illustrates how to apply CPU Rewrite Mode.

2.0 Introduction

The Renesas M16C/62 is a 16-bit MCU, based on the M16C CPU core, with 256k bytes of user flash. The device can erase and program the on-chip flash memory under control of a user's program with no external programming devices required. This feature is called "CPU Rewrite Mode".

The premise for CPU Rewrite Mode is that applications may require nonvolatile storage of data. In general, this could be data acquisition, configuration parameters, hours in service, and so on.

3.0 Background

The M16C/62 has two other flash programming modes: Parallel I/O Mode, and Standard Serial I/O Mode. Because these modes are mainly for programming the application code into the flash, details are not discussed in this article.

To use CPU Rewrite Mode, the memory structure and the control registers need to be identified. The memory map of the M16C/62 is shown in Figure 1. Note that the flash is divided into blocks such that certain erase/programming functions are done on a block basis. The boot flash area is used for serial I/O mode and is not available for CPU Rewrite mode programming.

The "Flash Memory Control Register" (FMR0) is shown in Figure 2. Normally, only the first three LSBs are used for CPU rewrite mode.

Beyond CPU registers, the flash memory has its own logic to handle erase and programming procedures. This is the flash's "Write State Machine" (WSM). The WSM commands are given in Table 1.

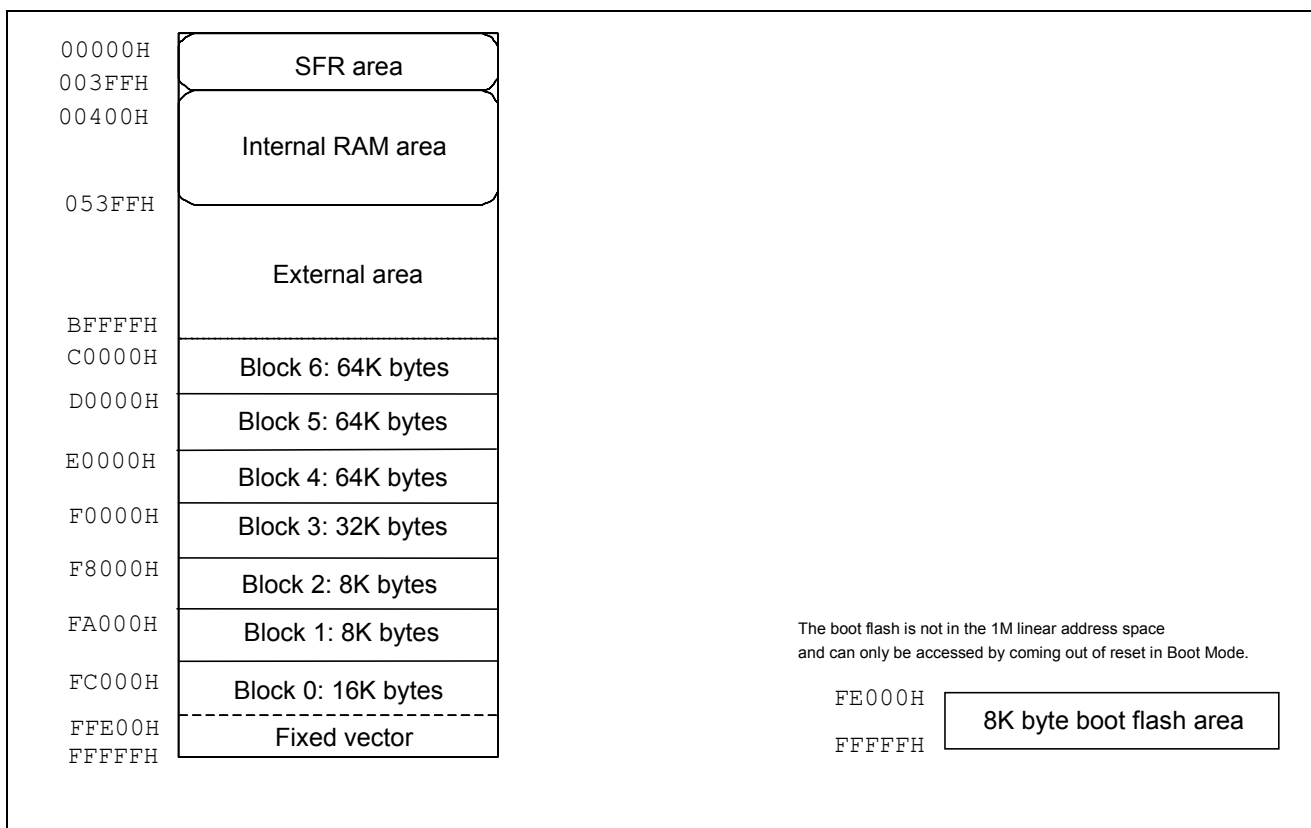


Figure 1 M16C/62 Memory Map

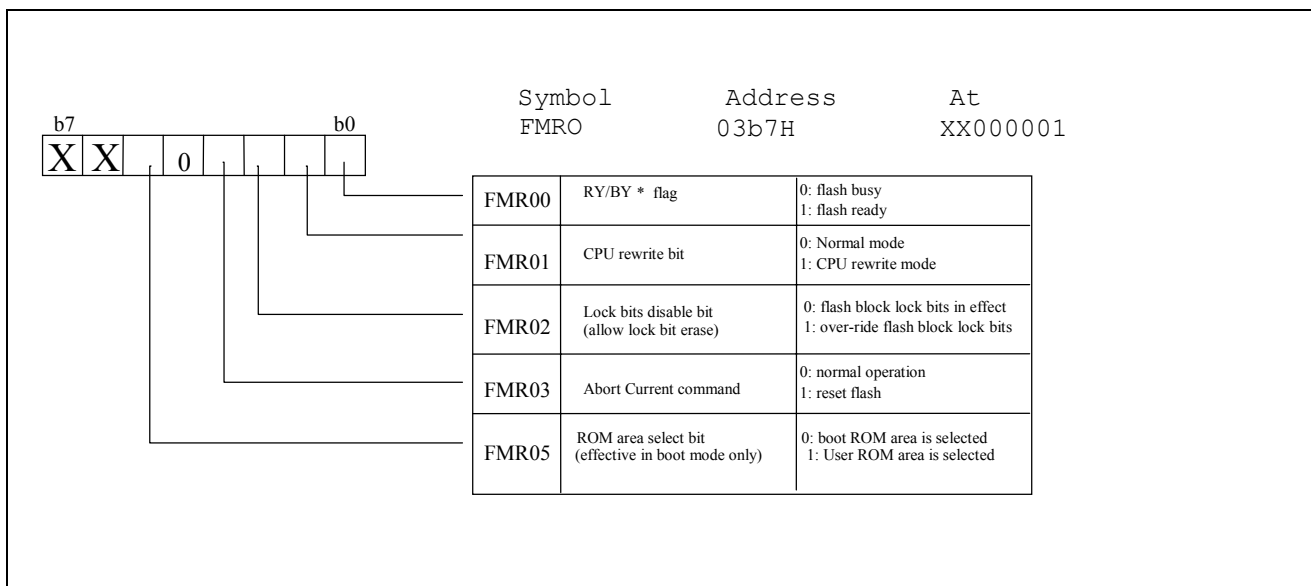


Figure 2 Flash Memory Control Register

Table 1 List of Software Commands (CPU Rewrite Mode)

Command	First bus cycle			Second bus cycle			Third bus cycle		
	Mode	Address	Data (D ₀ to D ₇)	Mode	Address	Data (D ₀ to D ₇)	Mode	Address	Data (D ₀ to D ₇)
Read array	Write	X (Note 6)	FF ₁₆						
Read status register	Write	X	70 ₁₆	Read	X	SRD (Note 2)			
Clear status register	Write	X	50 ₁₆						
Page program (Note 3)	Write	X	41 ₁₆	Write	WA0 (Note 3)	WD0 (Note 3)	Write	WA1	WD1
Block erase	Write	X	20 ₁₆	Write	BA (Note 4)	D0 ₁₆			
Erase all unlock block	Write	X	A7 ₁₆	Write	X	D0 ₁₆			
Lock bit program	Write	X	77 ₁₆	Write	BA	D0 ₁₆			
Read lock bit status	Write	X	71 ₁₆	Read	BA	D ₆ (Note 5)			

Note 1: When a software command is input, the high-order byte of data (D₈ to D₁₅) is ignored.

Note 2: SRD = Status Register Data

Note 3: WA = Write Address, WD = Write Data

WA and WD must be set sequentially from 00₁₆ to FE₁₆ (byte address; however, an even address). The page size is 256 bytes.

Note 4: BA = Block Address (Enter the maximum address of each block that is an even address.)

Note 5: D₆ corresponds to the block lock status. Block not locked when D₆ = 1, block locked when D₆ = 0.

Note 6: X denotes a given address in the user ROM area (that is an even address).

4.0 Flash Programming Basics

The flash must be programmed in 256-byte pages on page boundaries (A0 –A7 = 00 – FEh), 16 bits at a time. Attempts to program 8-bit data are ignored, and even commands must be set as 16-bit words. The flash can be “bulk” erased (‘erase all unlocked blocks’ command) or erased one block at a time (see memory map). Bit erase state = 1. Once a block is erased, individual pages can be programmed at any time. The CPU rewrite program can be stored in the flash, but because the WSM is common to all flash (all blocks), the CPU rewrite code cannot execute out of flash. The rewrite code must be transferred to RAM before it can be executed.

A generalized CPU Rewrite mode flowchart is shown in Figure 3. Note that before and after executing any program or erase command, the “Read Array” command is issued. This has the effect of resetting the flash control logic.

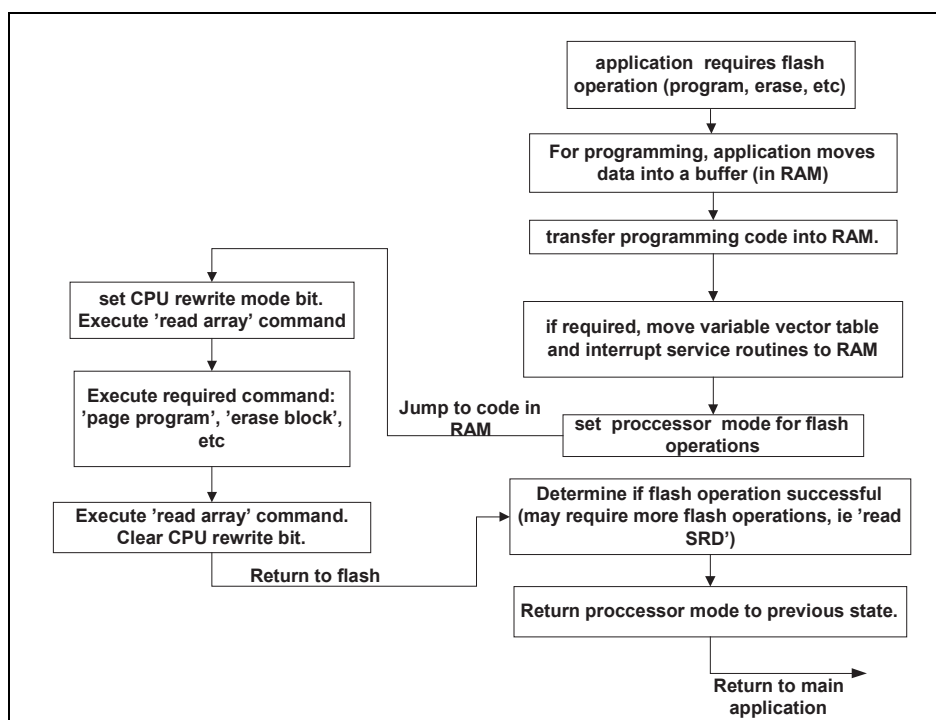


Figure 3 CPU Rewrite Mode Flowchart

5.0 Example Program

The example program was written to run on the MSV1632 Starter Kit but could be modified to implement in a user application. The program is written in C (Renesas' NC30 Compiler), with assembler used for the code executing out of RAM. This is a "no frills" program, but its main feature is that the code in RAM uses only about 160 bytes.

As illustrated in Figure 4, the program erases a block, programs a page, locks a block, and then unlocks the block. The block is unlocked because locked blocks are not compatible with the Starter Kit's debugger, KD30. Note in the assembler code that after the CPU Rewrite bit is cleared, the Reserve bit is set. This is required because clearing the CPU Rewrite bit automatically clears the Reserve bit. The Reserve bit is used for compatibility between other M16C derivatives. For consistent operation of the M16C/62 in single chip mode, this bit is set before returning to the flash area. See the M16C/62 data sheets for more information.

5.1 Compatibility

This program is compatible with M16C/6x microcontrollers with page write (256 bytes) flash memory. It is NOT compatible with word write MCUs such as the M16C/62P series. The driver is compatible with the above noted MCUs on any Starter Kit/evaluation system running under the KD30 debugger. It CANNOT be evaluated or demonstrated on any emulator using RAM to emulate flash (i.e., Renesas' PC4701, Nohau, or Ashling emulator systems).

5.2 Demonstrating the Program

Under KD30, the RAM buffer (at 2000h) can be edited, the program run, and the flash viewed. Note that viewing the C Watch -> Globals window will produce the status of the flash (SRD) and the lock bit status.

6.0 Alternate Implementation

To program the flash, 256 bytes must be sent to the flash at a time. However, not all 256 bytes need to be programmed at the same time. If only part of a page is to be programmed, the remaining bytes are sent FFh (erase state). At a later time, more bytes can be programmed using the following steps:

1. Copy the partly programmed flash page to a 256-byte RAM buffer.
2. Insert the bytes to be programmed into the RAM buffer.
3. Write the RAM buffer to flash.

It must be noted that each time a page is programmed, it should be considered as another erase/program cycle.

7.0 Reference

Renesas Technology Corporation Semiconductor Home Page

<http://www.renesas.com>

E-mail Support

support_apl@renesas.com

Data Sheets

M16C/62 datasheets, 62aeds.pdf

User's Manual

- 6020esm.pdf (Software Manual)
- 6020ec.pdf (C Manual)
- 6020easm.pdf (Assembler Manual)
- NC30ue.pdf (Compiler Manual)

8.0 Appendix

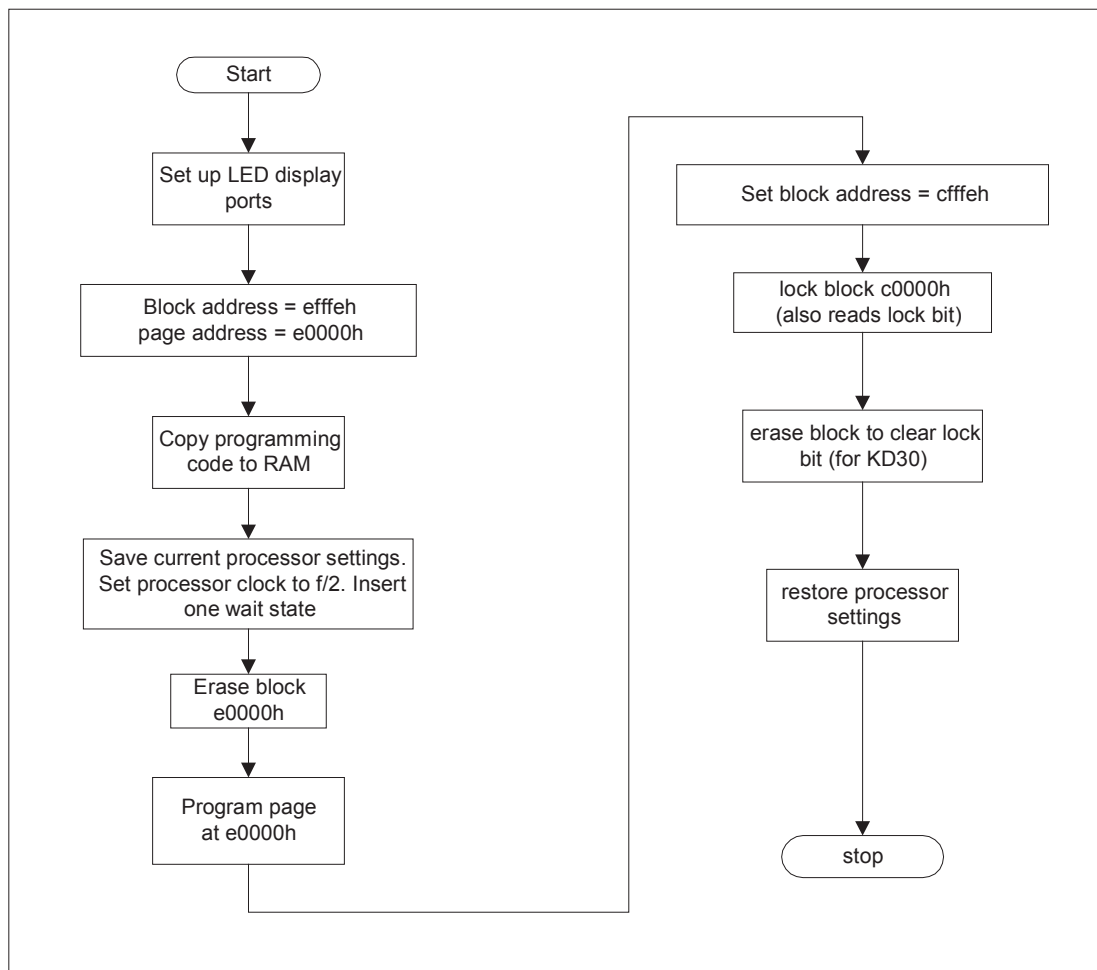


Figure 4 Example Program Flowchart: Main C Routine

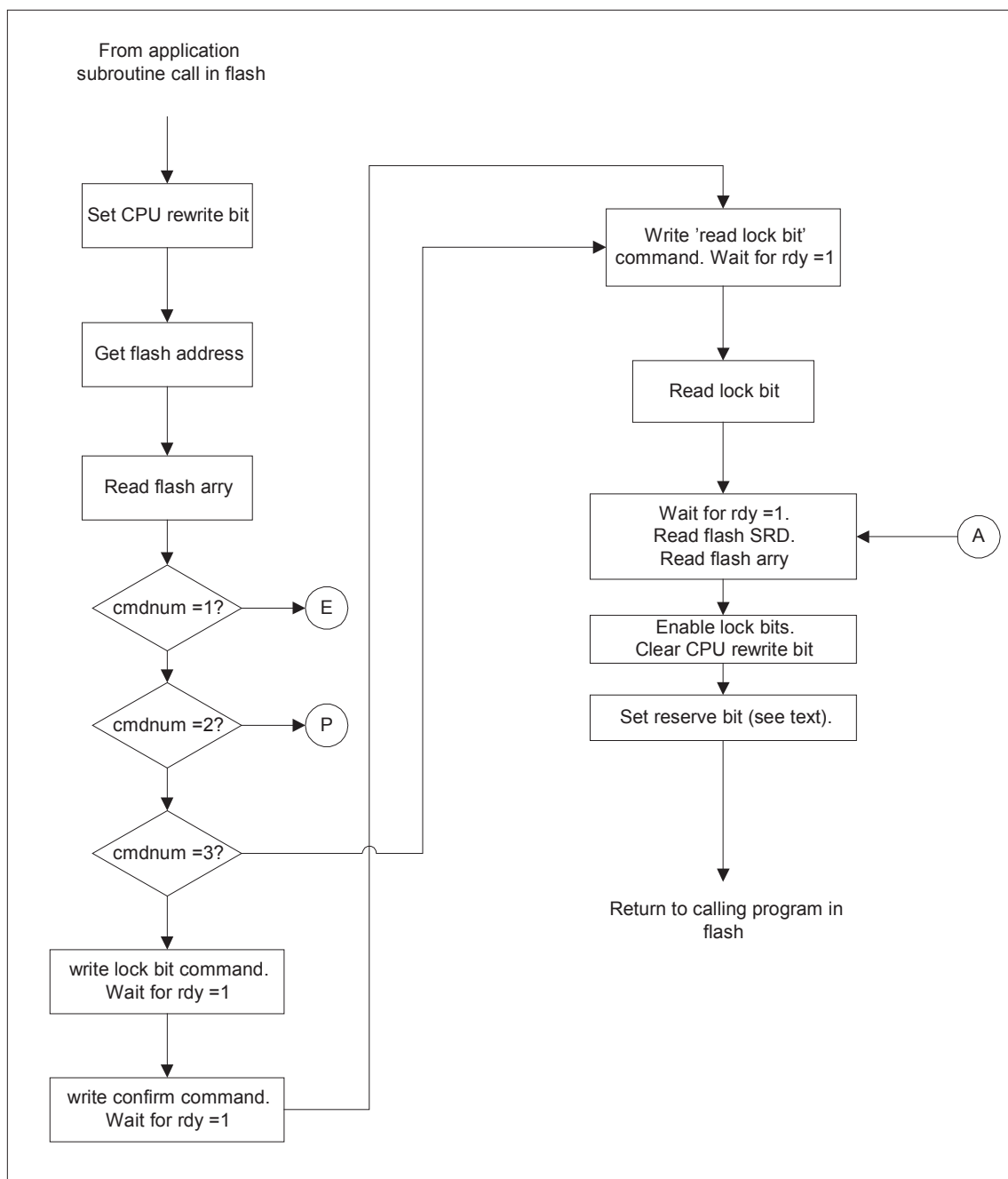


Figure 5 Example Program Flowchart: Assembler Code in RAM. Page 1

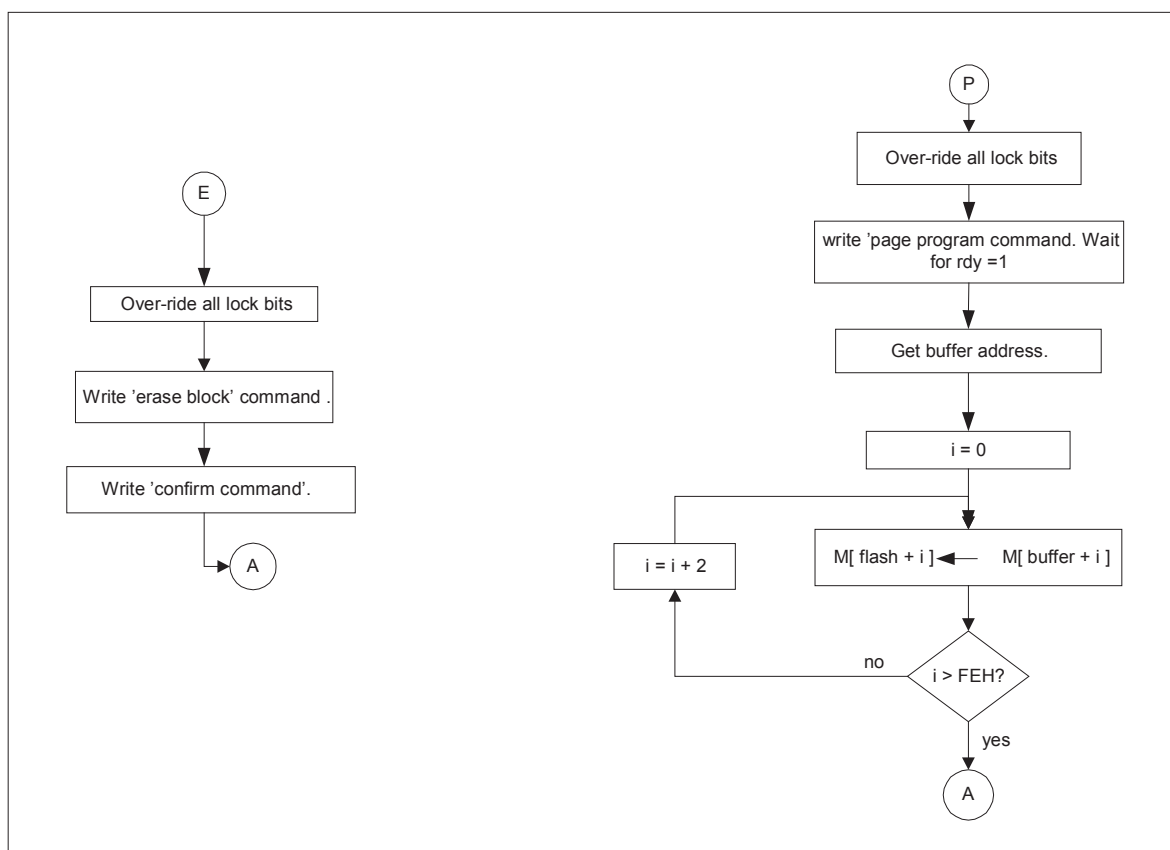


Figure 6 Example Program Flowchart: Assembler Code in RAM. Page 2

9.0 Software Code

```

/*****
*
*
*   File Name: cpu_rw62.c
*
*   Content: CPU REWRITE PROGRAMMER version 2.1
*            Compiled with KNC30 ver. 3.20.00.
*
*   Demonstrates CPU rewrite mode on the M16C/62
*   microcontroller. This program was designed to
*   operate on any M16C/62 starter kit, using the KD30 debugger.
*   Note it is NOT compatible with emulators such as
*   Renesas's PC4701 series that use RAM to emulate flash ROM.
*
*   It is intended that the program executes out of the D0000h block
*   as blocks C0000h and E0000h are erased and programmed.
*
*   The program also demonstrates how to mix assembler
*   and C code using Renesas's NC30 compiler.
*
*
*****/

```

```
* Copyright,2003 RENESAS TECHNOLOGY CORPORATION
*
*
* note:
*   Renesas Technology Corporation does not guarantee the performance or
*   use of this source-code. The intended use of provided source-code is the
*   sole responsible of the user. The files have been successfully compiled
*   using Renesas's NC30 compiler. Before using this software review the
*   source and make any necessary changes to support your hardware and
*   application.
*
*=====
*   $Log:$
*=====*/
#define aerase 1 //set cmdnum to one of these 'a' values
#define aprogram 2
#define areadloc 3
#define alocblock 4

#define wait1 0x8e00 // processor mode value for 1 wait state

#define interrupton _asm (" fset i") // "macro" assembler code
#define interruptoff _asm (" fclr i")

#define RAMBUFFLOC 0x2000 //location of ram buffer (for programming flash)

#pragma ADDRESS ramcode 1000h // address in RAM for CPU rewrite code
#pragma ADDRESS prcr 00ah // SFR's
#pragma ADDRESS cm0 006h
#pragma ADDRESS cm1 007h
#pragma ADDRESS pm01 004h

unsigned int ram_buff; // assembler "pointer" to RAM buffer
unsigned long int flsh_addr; // assembler "pointer" to flash page/block
extern far int copy_strt,copy_end;
far volatile int *ramxfer,*romxfer;
volatile int pm01;
int pm01sav;

char cm0sav,cm1sav;
char flsh_stat,cmdnum,lokbitstat;
volatile char cm0,cm1,prcr,port0,port1,dir_p0,dir_p1;

// function prototypes
void asm_block(void);
void ramcode(void); // From the 'pragma' above, C considers "ramcode"
//just as any other label in memory.

void transfer(void);
void cpu_ini(void);
void eraseblock(unsigned long int);
void writepage(unsigned long int);
void lockblock(unsigned long int);
void cpu_rstor(void);
void lockbitstat(unsigned long int);
```

```

/*****
Name:      asm_block()

Parameters:
    inputs: globals only: cmndnum - 1 = erase block
                                   2 = program page
                                   3 = read lock bit status (default command)
                                   4 = lock block, includes read lock bit status

                                   flsh_addr - the block or page to be operated on
                                   ram_buff  - points to the 256 bytes of data to be
                                                programmed
                                                (required only for program page command)

Returns: nothing
    modifies: global flsh_stat - the flash SRD status byte after performing command
              global lokbitstat - if bit6 (D6) = 1, block unlocked,
                                   if bit6 = 0, block locked.

Description: CPU rewrite assembler code. The following 'block' of assembler
              code is moved to RAM then executed out of RAM. The assembler
              code is relocatable and command functions are generic enough
              to be implemented in a user application. Although not required
              for the starter kit, the erase and program routines disable
              the lock block bits.
              Ram usage approx. 160 bytes.
*****/

void asm_block(void)    // clean place for the assembler code, but function
                        // not required.
{
#pragma      ASM                // 'ASM' must be in upper case

;flash memory commands
rd_fstat      .equ    0070h
wrt_cmd       .equ    0041h
erase_cmd     .equ    0020h
cfm_cmd       .equ    00D0h
lok_cmd       .equ    0077h
rlok_cmd      .equ    0071h
rda_cmd       .equ    00ffh

fmr0          .equ    03b7h    ;M16C\62 flash control register
bsy_rdy       .btequ    0,fmr0
cpu_rwrt      .btequ    1,fmr0
lock_dis      .btequ    2,fmr0

```

```

flsh_rst          .btequ      3,fmr0
resbit            .equ        3      ; reserve area bit

_copy_strt:
; first do instructions common to all commands (save RAM space)
        bclr        cpu_rwrt
        bset        cpu_rwrt      ;set CPU rewrite mode
        mov.w       _flsh_addr+2,a1
        mov.w       _flsh_addr,a0 ;get block address
; sequence to reset flash
        mov.b       #rda_cmd,r0l  ; Read array resets flash
        jsr         Command_write

;  decode command
        cmp.b       #aerase,_cmndnum
        jeq         eraseflsh     ;erase block?
        cmp.b       #aprogram,_cmndnum
        jeq         progflsh     ;write page?
        cmp.b       #alocblock,_cmndnum
        jeq         lockflshblk  ;lock block?
        jmp         readlokstat   ;default:read lock bit

lockflshblk:
        mov.b       #lok_cmd,r0l
        jsr         Command_write ;send lock command
        mov.b       #cfm_cmd,r0l
        jsr         Command_write ;send confirm byte
                                   ;fall into read lock bit

readlokstat:
        mov.b       #rlok_cmd,r0l
        jsr         Command_write ;read lock bit
        lde.w       [a1a0],r0
        mov.b       r0l,_lokbitstat

        jmp         flsh_bsy      ;lock/read  command sent,
                                   ;now wait for flash ready then exit

eraseflsh:
        bclr        lock_dis
        bset        lock_dis     ;unlock all blocks

        mov.b       #erase_cmd,r0l
        ste.w       r0,[a1a0]    ;send erase command
        mov.b       #cfm_cmd,r0l
        ste.w       r0,[a1a0]    ;send confirm byte
;erase command sent, now wait for
;flash ready then exit (fall into flsh_bsy)

flsh_bsy:
        btst        bsy_rdy
        jeq         flsh_bsy

        mov.w       #rd_fstat,r1
        ste.w       r1,[a1a0]
        lde.w       [a1a0],r1

```

```

                                mov.b      r1l,_flsh_stat ; get status (SRD) of
                                                ; last operation (error checking)

                                mov.b      #rda_cmd,r0l   ; Read array resets flash
                                jsr        Command_write
                                bclr       lock_dis
                                bclr       cpu_rwrt
                                bset       resbit,_pm01+1 ;above instruction clears
                                                ;this bit!!!

                                rts                    ;return to ROM area

progflsh:
                                bclr       lock_dis
                                bset       lock_dis        ;unlock all blocks
                                mov.b      #wrt_cmd,r0l    ;Page program command
                                jsr        Command_write
                                mov.w      _ram_buff,r1    ;get ram buffer address

prog_loop:
                                xchg.w     r1,a0           ;save flash address
                                mov.w      [a0],r3         ;get data
                                xchg.w     r1,a0           ;get write to address
                                ste.w      r3,[a0]         ;and write
                                add.w      #2,r1
                                add.w      #2,a0
                                tst.b      #0ffh,a0
                                jnz        prog_loop
                                jmp        flsh_bsy        ;write page command
                                                ;complete, now wait
                                                ;for flash ready then exit

Command_write:
                                btst       bsy_rdy        ; wait for flash ready
                                jz         Command_write
                                ste.w      r0,[a0]        ; write command to flash WSM
                                rts

_copy_end:
#pragma ENDASM

}

```

/******

Name: Main()

Parameters: none

Returns: nothing

Description: Main program. For demonstration purposes, the main program erases the E0000H - EFFFFH block then writes the contents of ram_buff to the first (256 byte) page in that block. Ram_buff was given an absolute address (2000H) such that under KD30, the buffer could be edited, program run, then the flash viewed to see that it programmed. To use this program with KD30 on a Starter Kit, run the program in "free run"

mode and do a "go free". Hit the reset icon on KD30. At this point the flash can be viewed. Note that when you reload a program into flash, KD30 erases the entire user flash.

Notes on lock bit. WARNING!! locking a block IS NOT compatible with KD30 and the ROM monitor. If you lock any block and attempt to download your program to the flash, it will mess up the ROM monitor and you will need to reprogram the ROM monitor back into the M16C/62 (i.e. using flashwriter). The lock disable bit in the 'flash memory control register' only over-rides the lock bits, not clear them. The only way to clear a lock bit is to erase the associated block. This example operates on a 'dummy' block for demonstrating lock bit programming.

It is up to the main program (and user) to ensure that valid addresses are passed to the commands (no error checking). The assembler code supports reading the flash status (SRD) but main() doesn't use it.

```

*****/

void main(void)
{
    long maxb_addr,writ_addr;

    maxb_addr = 0xefff;           // for erasing
    writ_addr = 0xe000;          // page to program
    transfer();                  // transfer assembler program to ram
    cpu_ini();                   // set processor for programming
    eraseblock(maxb_addr);
    writepage(writ_addr);        // assumes data in buffer, fill via KD30.

    // Now demonstrate locking a block, under KD30, view global 'lokbitstat'
    maxb_addr = 0xdfff;
    lockblock(maxb_addr);        // also reads lock bit into 'lokbitstat'
    eraseblock(maxb_addr);       // clears lock bit..VERY Important for KD30! see
                                //above text on lock bit.
    cpu_rstor();                 // restore processor modes

    while(1)
    {    //good ending
    }
}

/*****
Name:      transfer()
Parameters: none
Returns:   nothing
Description: Copies assembler code to program the flash into RAM
*****/

void transfer(void)
{

```

```

    romxfer = &copy_strt;           // point to assembler code in flash area
    ramxfer = (far int *)&ramcode;  // point to RAM where code is to be executed
                                    // from (get compiler warning if don't
                                    // typecast)

    while (romxfer < &copy_end)
    {
        *ramxfer = *romxfer;
        ramxfer++;
        romxfer++;
    }
}

/*****
Name:      void cpu_ini(void)
Parameters: none
Returns:   nothing
Description: Sets the processor mode for programming flash. A wait state is
            added and the clock is set to the input frequency/2 (Xin/2).
            Original configuration saved in globals: cm0sav, cm1sav, pm01sav.
*****/

void cpu_ini(void)
{
    cm0sav = cm0;    // save current CPU modes and clock setting
    cm1sav = cm1;
    pm01sav = pm01;
    prcr = 3;        // protect off
    pm01 = wait1;     // insert wait state
    cm1 = 0x60;        // divide CPU clock by 2
    cm0 = 0x08;        // ensure high drive on clock
    prcr = 0;         // protection back on
}

/*****
Name:      void eraseblock(unsigned long int)
Parameters: maxb_addr
Returns:   nothing, modifies global 'flsh_stat'
Description: Erases the flash block at maxb_addr. maxb_addr is the last
            (even) address in the block to be erased
*****/

void eraseblock(unsigned long int maxb_addr)
{
    flsh_addr = maxb_addr;
    cmdndnum = aerase;
    interruptoff;
    ramcode();
    interrupton;
}

```



```

/*
/*****
Name:      void writepage(unsigned long int )
Parameters: writ_addr
Returns:    nothing, modifies global 'flsh_stat'
Description: writes a 256 byte page in flash, starting at address writ_addr.
              Function has fixed the ram buffer at RAMBUFFLOC for demonstration
              purposes.
*****/

void writepage(unsigned long int writ_addr)
{
    flsh_addr = writ_addr;
    ram_buff = RAMBUFFLOC;
    cmdnum = aprogram;
    interruptoff;
    ramcode();
    interrupton;
}

/*****
Name:      lockblock(unsigned long int )
Parameters: maxb_addr
Returns:    nothing, modifies globals 'lokbitstat','flsh_stat'
Description: Programs the lock bit for the block at maxb_addr.  maxb_addr is
              the last (even) address in the block.
*****/

void lockblock(unsigned long int maxb_addr)
{
    flsh_addr = maxb_addr;
    cmdnum = alockblock;
    interruptoff;
    ramcode();
    interrupton;
}

/*****
Name:      cpu_rstor(void)
Parameters: none
Returns:    nothing
Description: Restores the processor mode back to original speed.
*****/

```

```
void cpu_rstor(void)
{
// restore CPU & clock settings
prcr = 3;                // protect off
pm01 = pm01sav;
cm1 = cm1sav;
cm0 = cm0sav;
prcr = 0;                // protection back on
}

/*****
Name:      lockbitstat(unsigned long int)
Parameters: maxb_addr
Returns:   nothing, modifies globals 'lokbitstat','flsh_stat'
Description: Reads lock bit status determined by maxb_addr into global
              'lokbitstat'. maxb_addr is the last (even) address in the block.
*****/

void lockbitstat(unsigned long int maxb_addr)
{
    flsh_addr = maxb_addr;
    cmdnum = areadloc;
    interruptoff;
    ramcode();
    interrupton;
}
```

Keep safety first in your circuit designs!

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